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Electronic Supplementary Information for

High-Performance p-Type Thin Film Transistors Using Atomic-Layer-Deposited SnO Films

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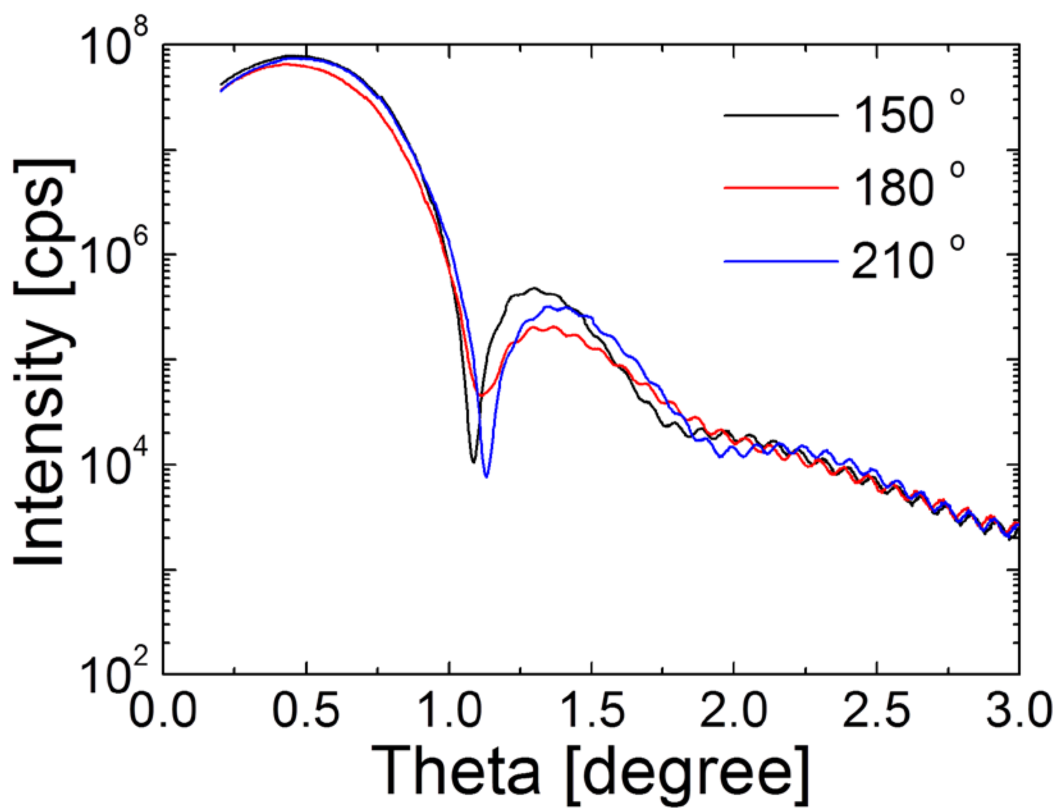

Figure S1. X-ray reflectivity spectra of the SnO films grown at 150, 180, and 210 °C. The densities of the SnO films, which is evaluated from a critical angle in the graph, are approximately 5.5 – 5.6 gcm^{-3}. Negligible difference in the film density is observed in terms of the growth temperature.

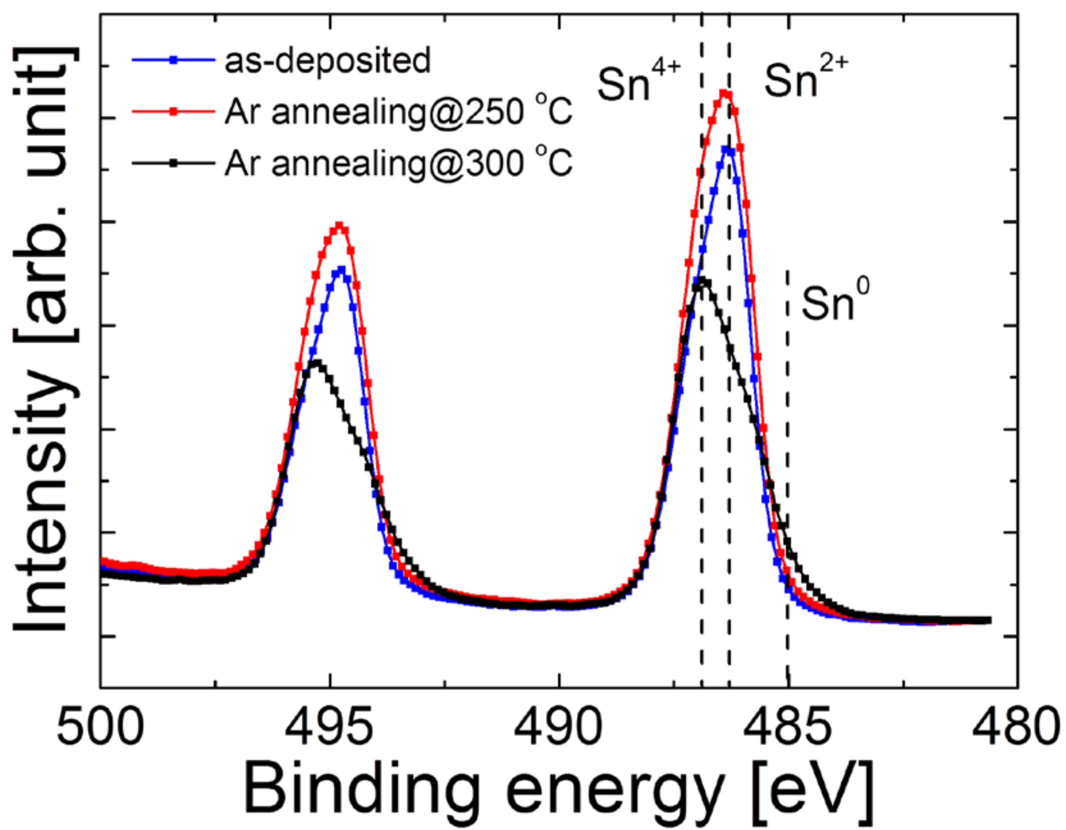

Figure S2. X-ray photoelectron Sn 3d spectra of the as-grown SnO film and the post-annealed SnO films at 250 and 300 °C under Ar atmosphere.

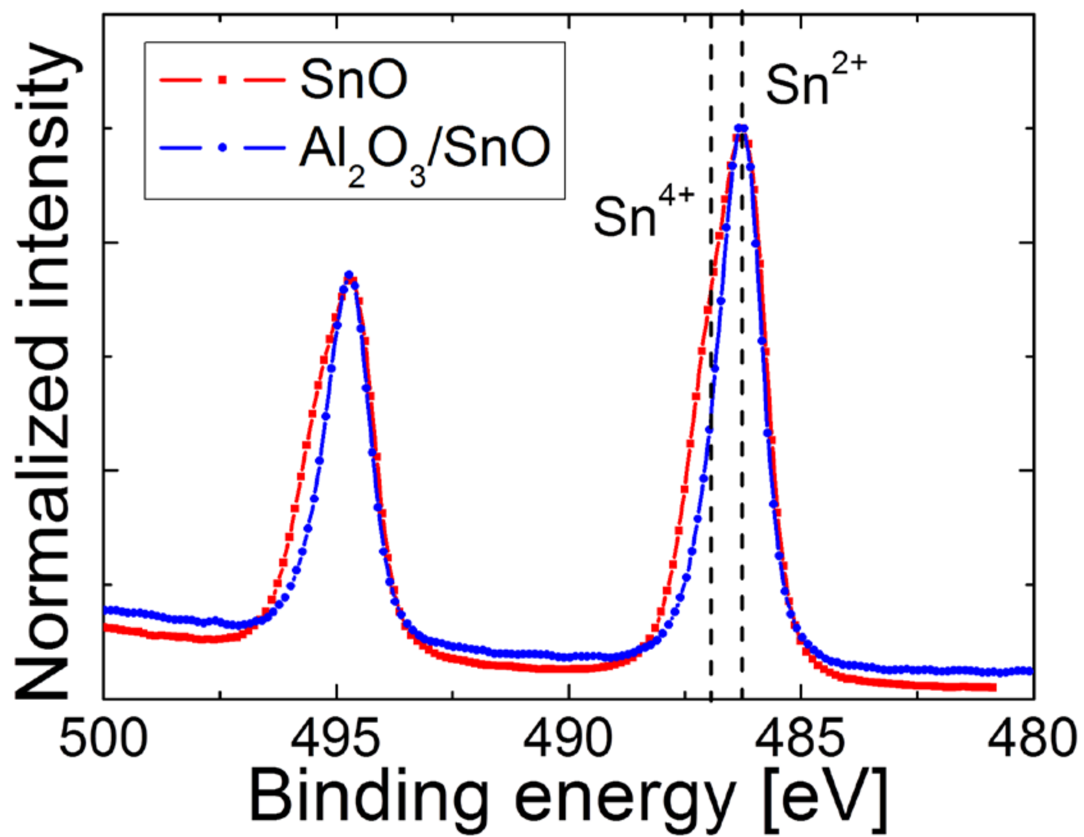

Figure S3. X-ray photoelectron Sn 3d spectra of the un-passivated SnO film and the 1.5 nm-thick Al_2O_3 coated SnO film.